

Product Summary

| $V_{(BR)DSS}$ | $R_{DS(on)}$ max | I_D max $T_A = +25^\circ C$ |
|---------------|--------------------------------|----------------------------------|
| 30V | 28m Ω @ $V_{GS} = 10V$ | 5.8A |
| | 42m Ω @ $V_{GS} = 4.5V$ | 4.8A |
| | 82m Ω @ $V_{GS} = 3V$ | 2.0A |

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

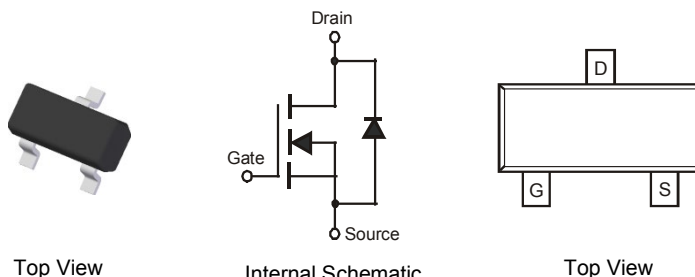
Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMN3404LQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Case: SOT23 (Standard)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)

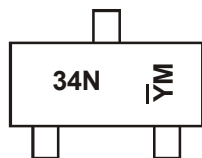


Ordering Information (Note 4)

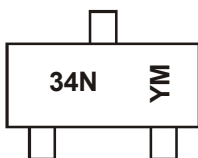
| Part Number | Compliance | Case | Packaging |
|-------------|------------|------------------|------------------|
| DMN3404L-7 | Standard | SOT23 (Standard) | 3000/Tape & Reel |
| DMN3404LQ-7 | Automotive | SOT23 (Standard) | 3000/Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 5. For packaging details, go to Diodes website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



Chengdu A/T Site



Shanghai A/T Site

34N = Product Type Marking Code
 YM = Date Code Marking for SAT (Shanghai Assembly/Test site)
 $\bar{Y}M$ = Date Code Marking for CAT (Chengdu Assembly/Test site)
 Y or \bar{Y} = Year (ex: I = 2021)
 M = Month (ex: 9 = September)

Date Code Key

| Year | 2009 | | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 | 2030 |
|------|------|-------|------|------|------|------|------|------|------|------|------|------|
| Code | W | | I | J | K | L | M | N | O | P | R | S |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | O | N | D |

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | | Symbol | Value | Units |
|---------------------------------------------------|--------------|---------------------------|----------|-------|
| Drain-Source Voltage (Notes 6, 7) | | V_{DSS} | 30 | V |
| Gate-Source Voltage | | V_{GSS} | ± 20 | V |
| Continuous Drain Current (Note 6) $V_{GS} = 10V$ | Steady State | $T_A = -40^\circ\text{C}$ | 4.6 | A |
| | | $T_A = +25^\circ\text{C}$ | 4.2 | |
| | | $T_A = +85^\circ\text{C}$ | 3.0 | |
| Continuous Drain Current (Note 7) $V_{GS} = 10V$ | Steady State | $T_A = -40^\circ\text{C}$ | 6.2 | A |
| | | $T_A = +25^\circ\text{C}$ | 5.8 | |
| | | $T_A = +85^\circ\text{C}$ | 4.0 | |
| Continuous Drain Current (Note 7) $V_{GS} = 4.5V$ | Steady State | $T_A = -40^\circ\text{C}$ | 5.2 | A |
| | | $T_A = +25^\circ\text{C}$ | 4.8 | |
| | | $T_A = +85^\circ\text{C}$ | 3.2 | |
| Continuous Drain Current (Note 7) $V_{GS} = 3V$ | Steady State | $T_A = -40^\circ\text{C}$ | 2.2 | A |
| | | $T_A = +25^\circ\text{C}$ | 2.0 | |
| | | $T_A = +85^\circ\text{C}$ | 1.0 | |
| Pulsed Drain Current | | I_{DM} | 30 | A |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|---------------------------------------------------------------------|-----------------|-------------|--------------------|
| Power Dissipation (Note 6) | P_D | 0.72 | W |
| Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ | $R_{\theta JA}$ | 173 | $^\circ\text{C/W}$ |
| Power Dissipation (Note 7) | P_D | 1.4 | W |
| Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ | $R_{\theta JA}$ | 90 | $^\circ\text{C/W}$ |
| Operating and Storage Temperature Range | T_J, T_{STG} | -55 to +150 | $^\circ\text{C}$ |

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|-------------------------------------------------------------------|---------------------|-----|-------|------|------|------------------------------------------------------------------------------------------|
| OFF CHARACTERISTICS (Note 8) | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 30 | — | — | V | V _{GS} = 0V, I _D = 250μA |
| Zero Gate Voltage Drain Current T _J = +25°C | I _{DSS} | — | — | 1.0 | μA | V _{DS} = 30V, V _{GS} = 0V |
| Gate-Source Leakage | I _{GSS} | — | — | ±100 | nA | V _{GS} = ±20V, V _{DS} = 0V |
| ON CHARACTERISTICS (Note 8) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | 1.0 | 1.5 | 2.0 | V | V _{DS} = V _{GS} , I _D = 250μA |
| Static Drain-Source On-Resistance T _J = -40°C (Note 9) | R _{DS(on)} | — | 23 | 27 | — | V _{GS} = 4.5V, I _D = 4.8A |
| | | — | 57 | 74 | — | V _{GS} =3V, I _D =2A |
| Static Drain-Source On-Resistance T _J = +25°C | R _{DS(on)} | — | 24 | 28 | mΩ | V _{GS} = 10V, I _D = 5.8A |
| | | — | 33 | 42 | | V _{GS} = 4.5V, I _D = 4.8A |
| | | — | 63 | 82 | | V _{GS} =3V, I _D =2A |
| Static Drain-Source On-Resistance T _J = +85°C (Note 9) | R _{DS(on)} | — | 71 | 95 | mΩ | V _{GS} =3V, I _D =2A |
| Forward Transfer Admittance | Y _{fs} | — | 10 | — | S | V _{DS} = 5V, I _D = 5.8A |
| Diode Forward Voltage | V _{SD} | — | 0.75 | 1.0 | V | V _{GS} = 0V, I _S = 1A |
| DYNAMIC CHARACTERISTICS (Note 10) | | | | | | |
| Input Capacitance | C _{iss} | — | 498 | — | pF | V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz |
| Output Capacitance | C _{oss} | — | 52 | — | pF | |
| Reverse Transfer Capacitance | C _{rss} | — | 45 | — | pF | |
| Gate Resistance | R _g | — | 1.75 | 2.8 | Ω | V _{DS} = 0V, V _{GS} = 0V, f = 1MHz |
| Total Gate Charge (V _{GS} = 3V) | Q _g | — | 3.8 | 5.3 | nC | V _{GS} = 3V, V _{DS} = 15V, I _D = 1A |
| Total Gate Charge (V _{GS} = 4.5V) | Q _g | — | 5.3 | 7.5 | nC | V _{GS} = 10V/4.5V, V _{DS} = 15V, I _D = 5.8A |
| Total Gate Charge (V _{GS} = 10V) | Q _g | — | 11.3 | 16 | nC | |
| Gate-Source Charge | Q _{gs} | — | 1.4 | — | nC | |
| Gate-Drain Charge | Q _{gd} | — | 2.1 | — | nC | V _{DD} = 15V, V _{GS} = 10V, R _L = 2.6Ω, R _G = 3Ω |
| Turn-On Delay Time | t _{D(on)} | — | 3.41 | 10 | ns | |
| Turn-On Rise Time | t _r | — | 6.18 | 13 | ns | |
| Turn-Off Delay Time | t _{D(off)} | — | 13.92 | 28 | ns | |
| Turn-Off Fall Time | t _f | — | 2.84 | 10 | ns | |

Notes: 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design and 25°C data. Not subject to production testing
 10. Guaranteed by design. Not subject to production testing.

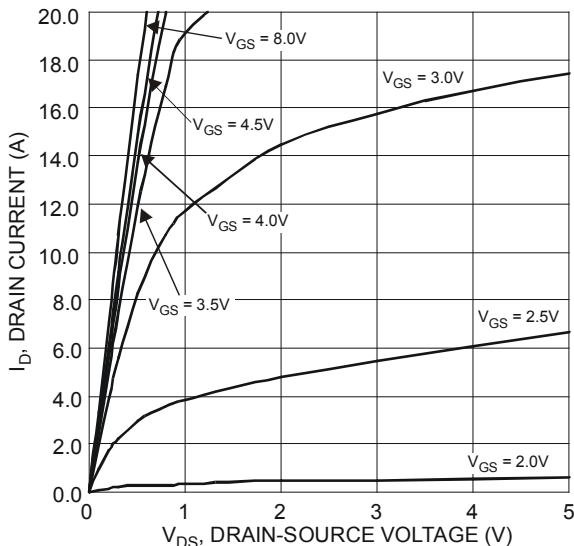


Figure 1 Typical Output Characteristics

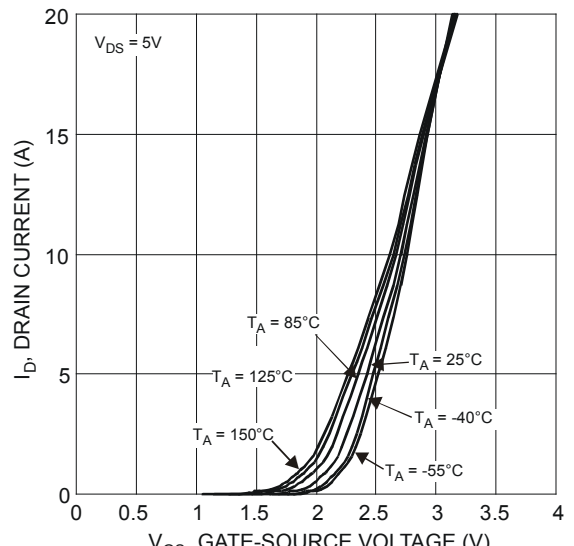


Figure 2 Typical Transfer Characteristics

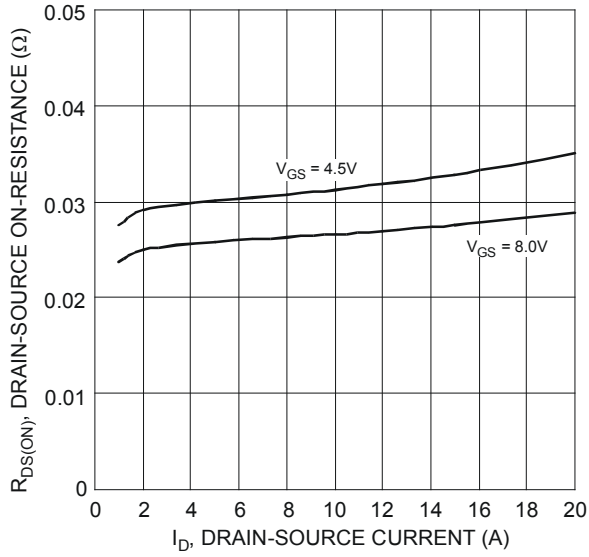


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

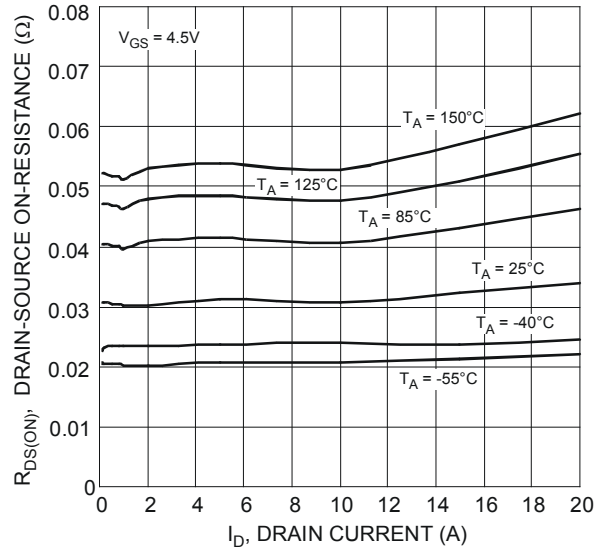


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

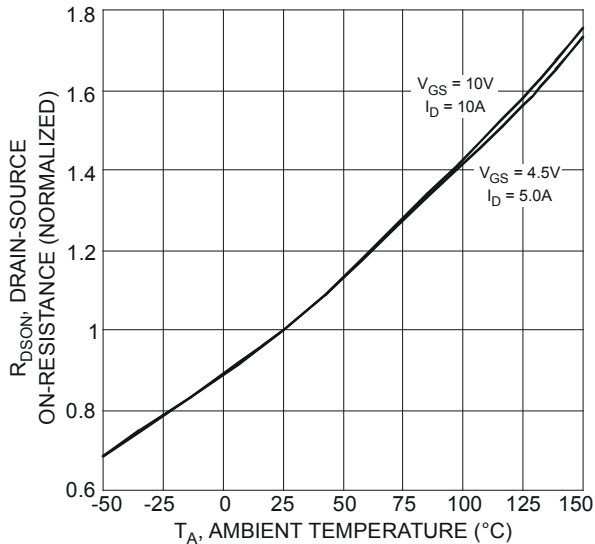


Figure 5 On-Resistance Variation with Temperature

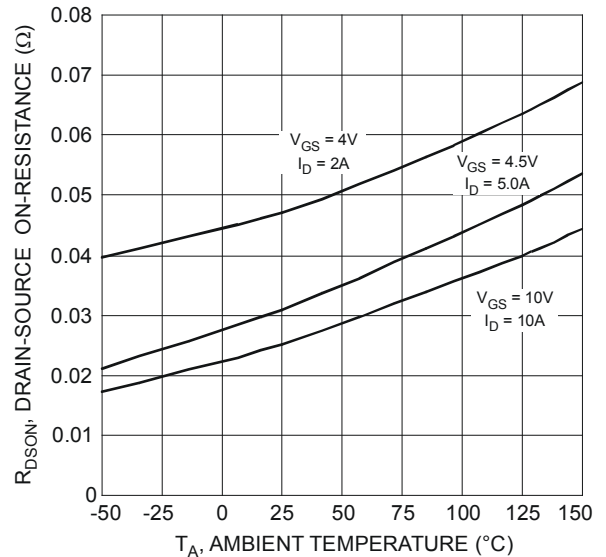


Figure 6 On-Resistance Variation with Temperature

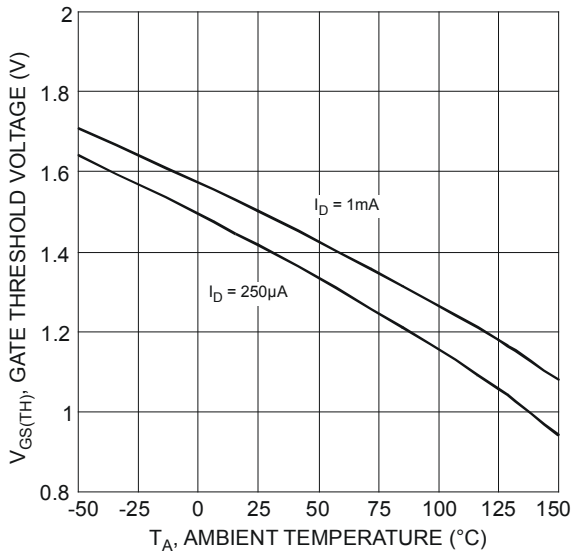


Figure 7 Gate Threshold Variation vs. Ambient Temperature

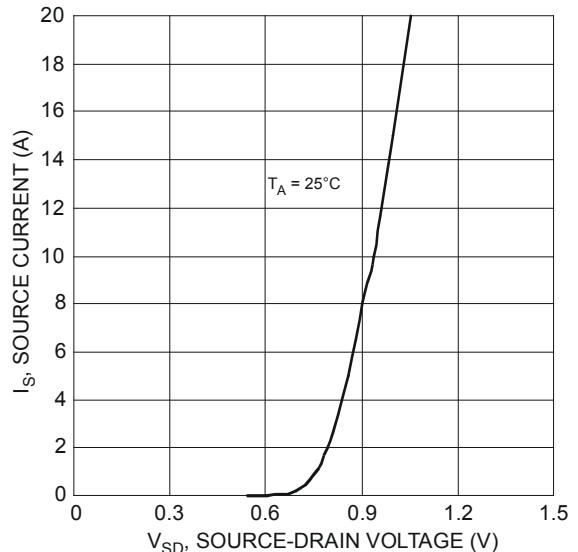
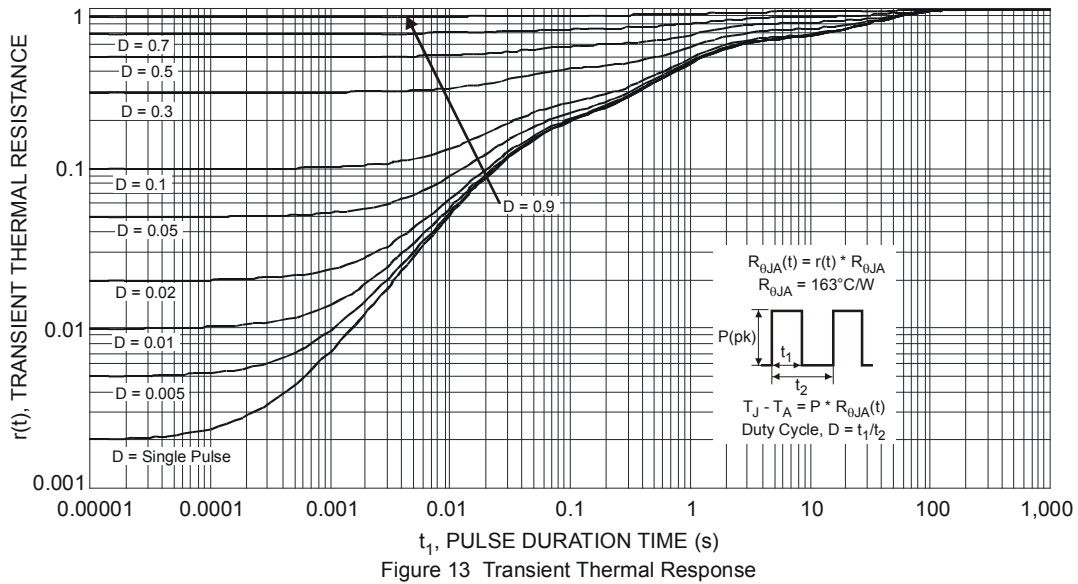
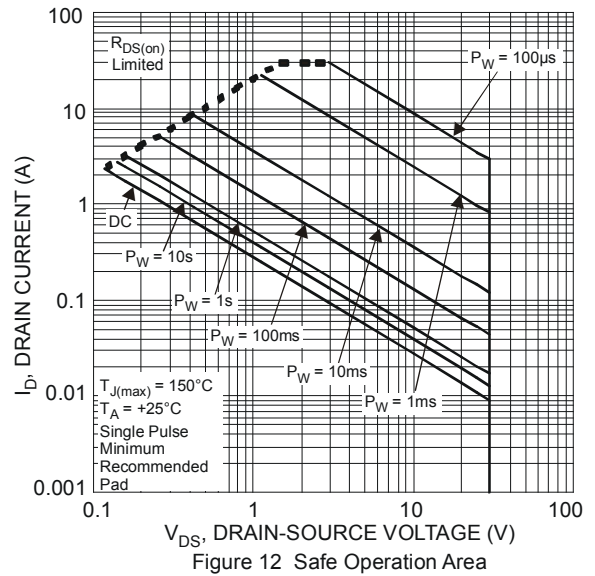
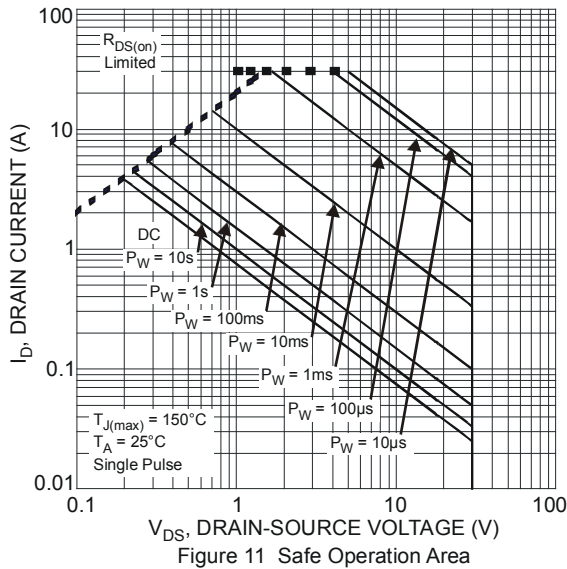
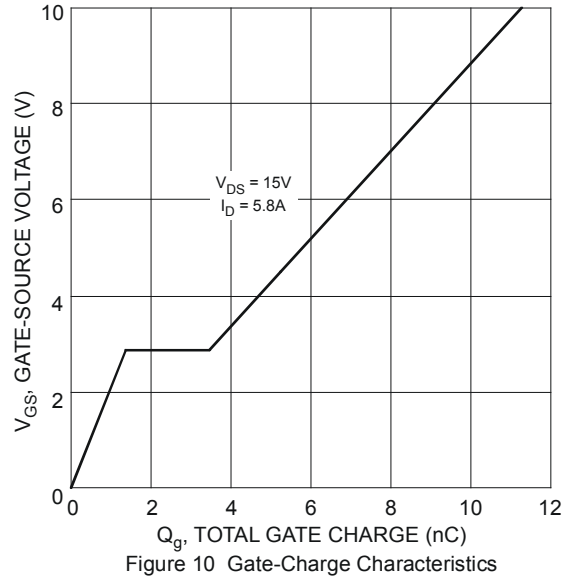
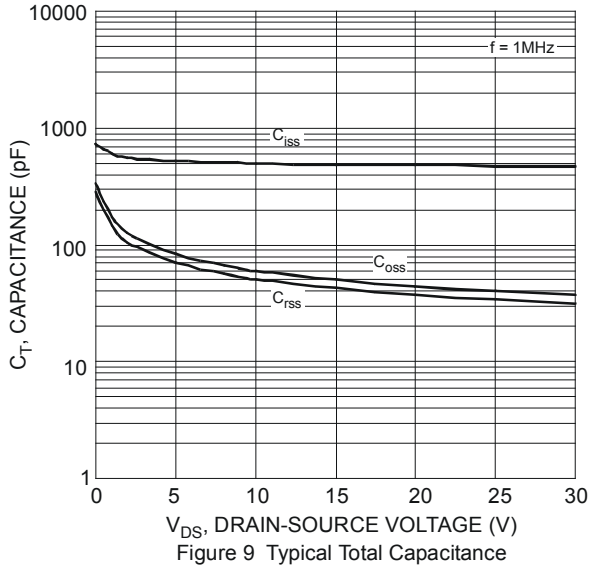
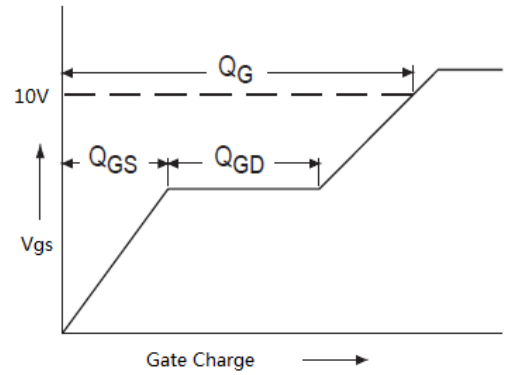
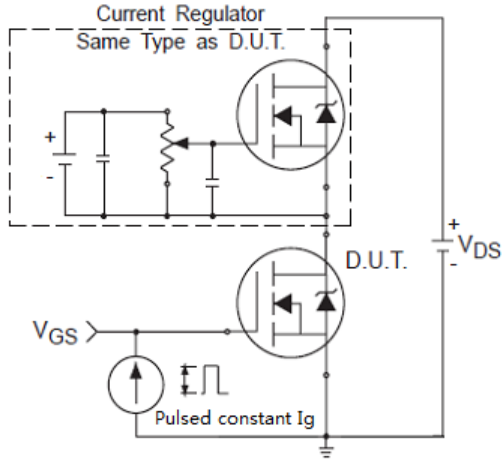


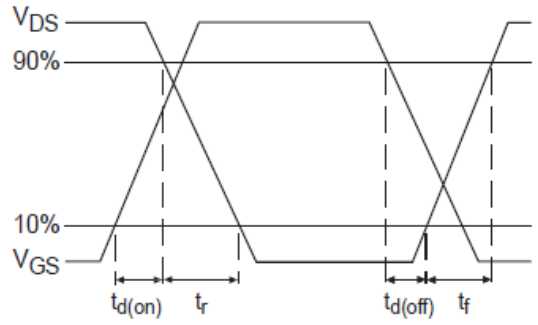
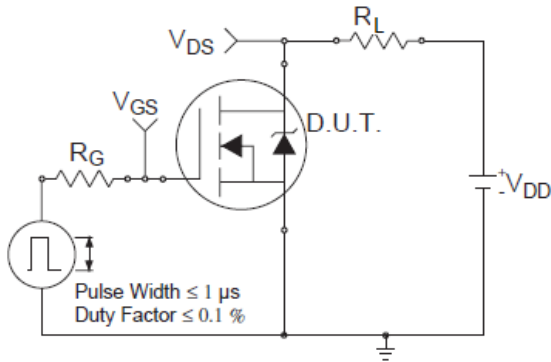
Figure 8 Diode Forward Voltage vs. Current



Gate Charge Test Circuit and Waveform



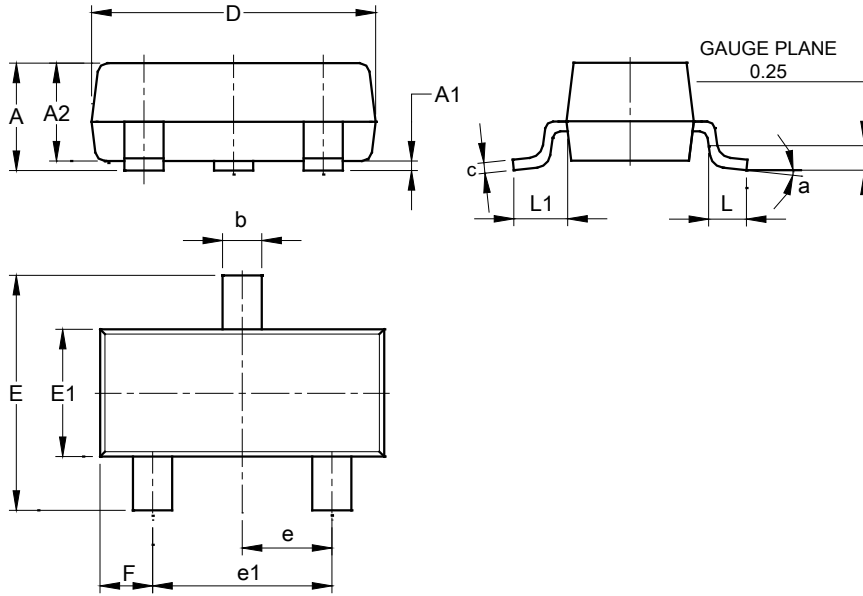
Switching Test Circuit and Waveform



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23 (Standard)

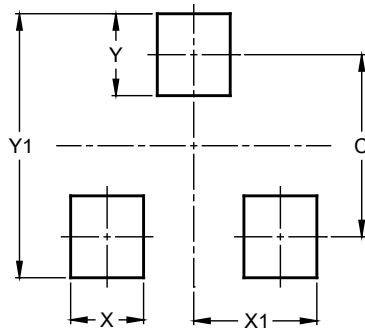


| SOT23 (Standard) | | | |
|----------------------|-------|-------|-------|
| Dim | Min | Max | Typ |
| A | 0.90 | 1.15 | 1.025 |
| A1 | 0.00 | 0.10 | 0.05 |
| A2 | 0.85 | 1.10 | 0.975 |
| b | 0.30 | 0.51 | 0.40 |
| c | 0.080 | 0.202 | 0.11 |
| D | 2.80 | 3.00 | 2.90 |
| E | 2.25 | 2.55 | 2.40 |
| E1 | 1.20 | 1.40 | 1.30 |
| e | 0.89 | 1.03 | 0.915 |
| e1 | 1.78 | 2.05 | 1.83 |
| F | 0.40 | 0.60 | 0.535 |
| L1 | 0.45 | 0.61 | 0.55 |
| L | 0.25 | 0.55 | 0.40 |
| a | 0° | 8° | -- |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23 (Standard)



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 2.0 |
| X | 0.8 |
| X1 | 1.35 |
| Y | 0.9 |
| Y1 | 2.9 |

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